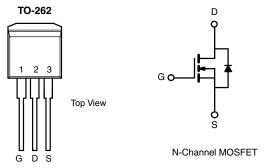


Vishay Siliconix

Automotive N-Channel 100 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	100				
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.0038				
I _D (A)	120				
Configuration	Single				



FEATURES

- TrenchFET® Power MOSFET
- Package with Low Thermal Resistance
- AEC-Q101 Qualifiedd
- 100 % R_a and UIS Tested
- Material categorization:
 For definitions of compliance please see www.vishay.com/doc?99912



FREE

ORDERING INFORMATION			
Package	TO-262		
Lead (Pb)-free and Halogen-free	SQV120N10-3m8-GE3		

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V_{DS}	100	V	
Gate-Source Voltage		V _{GS}	± 20		
Continuous Drain Current	T _C = 25 °C ^a	1	120		
Continuous Drain Current	T _C = 125 °C	I _D	102		
Continuous Source Current (Diode Conduction) ^a		Is	120	Α	
Pulsed Drain Current ^b		I _{DM}	480		
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	73		
Single Pulse Avalanche Energy	L = 0.1 IIII	E _{AS}	266	mJ	
Maximum Power Dissipation ^b	T _C = 25 °C	Pn	250	W	
	T _C = 125 °C	T P	83	VV	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to + 175	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient F	PCB Mount ^c	R_{thJA}	40	°C/W	
Junction-to-Case (Drain)		R _{thJC}	0.6	C/VV	

Notes

- a. Package limited.
- b. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- c. When mounted on 1" square PCB (FR-4 material).
- d. Parametric verification ongoing.



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static	•						
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0$, $I_D = 250 \mu A$		100	-	-	V
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$		2.5	3.0	3.5	V
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	-	± 100	nA
		$V_{GS} = 0 V$	V _{DS} = 100 V	-	-	1	
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 100 V, T _J = 125 °C	-	-	50	μA
		V _{GS} = 0 V	V _{DS} = 100 V, T _J = 175 °C	-	-	500	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 V$	120	-	-	Α
		V _{GS} = 10 V	I _D = 20 A	-	0.0030	0.0038	Ω
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 20 A, T _J = 125 °C	-	-	0.0064	
		V _{GS} = 10 V	I _D = 20 A, T _J = 175 °C	-	-	0.0080	
Forward Transconductance ^b	9 _{fs}	V _{DS}	V _{DS} = 15 V, I _D = 20 A		82	-	S
Dynamic ^b							
Input Capacitance	C _{iss}			-	5780	7230	
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	V _{GS} = 0 V V _{DS} = 25 V, f = 1 MHz		3070	3840	pF
Reverse Transfer Capacitance	C _{rss}			-	305	385	
Total Gate Charge ^c	Qg			-	125	190	
Gate-Source Charge ^c	Q _{gs}	V _{GS} = 10 V	$V_{DS} = 50 \text{ V}, I_{D} = 70 \text{ A}$	-	28	-	nC
Gate-Drain Charge ^c	Q_{gd}			-	46	-	
Gate Resistance	R_g		f = 1 MHz	1.6	3.3	5	Ω
Turn-On Delay Time ^c	t _{d(on)}			-	16	25	
Rise Time ^c	t _r	$V_{DD} = 50 \text{ V}, \text{ R}_L = 0.7 \Omega$ $I_D \cong 70 \text{ A}, V_{GEN} = 10 \text{ V}, \text{ R}_g = 1 \Omega$		-	110	165	ns
Turn-Off Delay Time ^c	t _{d(off)}			-	40	60	
Fall Time ^c	t _f			-	12	20	
Source-Drain Diode Ratings and Chara	acteristics ^b				•		
Pulsed Current ^a	I _{SM}			-	-	480	Α
Forward Voltage	V_{SD}	I _F = 100 A, V _{GS} = 0			0.9	1.5	V

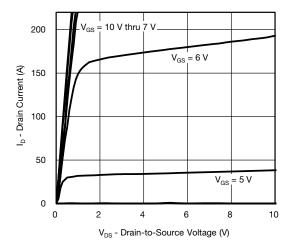
Notes

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

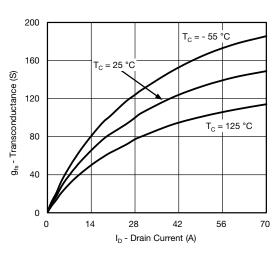
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



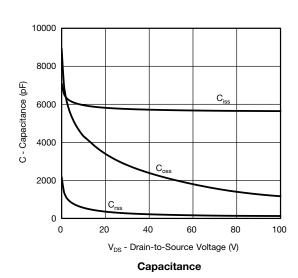
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

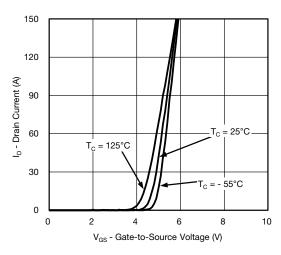


Output Characteristics

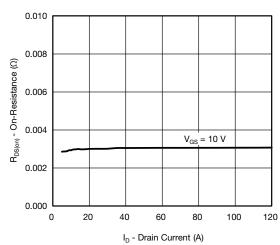


Transconductance

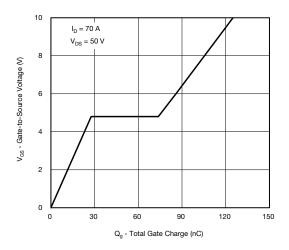




Transfer Characteristics



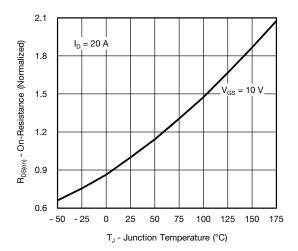
On-Resistance vs. Drain Current



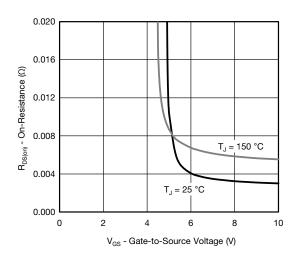
Gate Charge



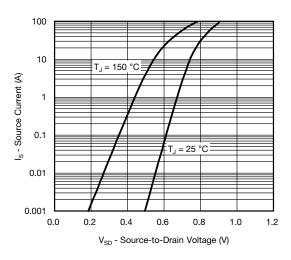
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



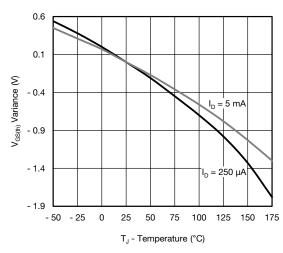
On-Resistance vs. Junction Temperature



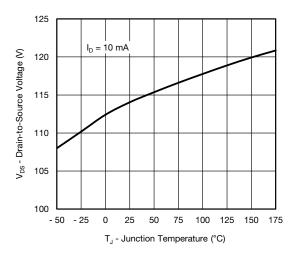
On-Resistance vs. Gate-to-Source Voltage



Source Drain Diode Forward Voltage



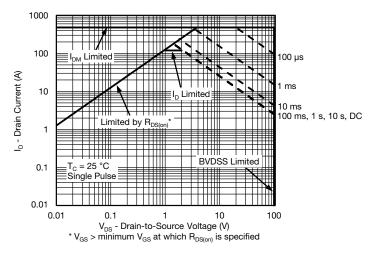
Threshold Voltage



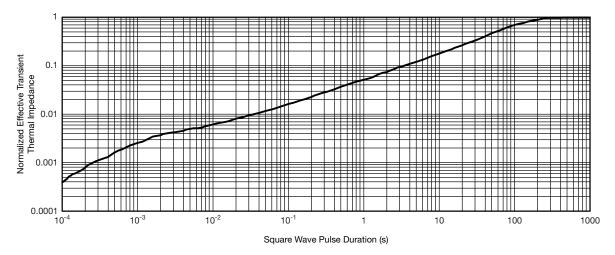
Drain Source Breakdown vs. Junction Temperature



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



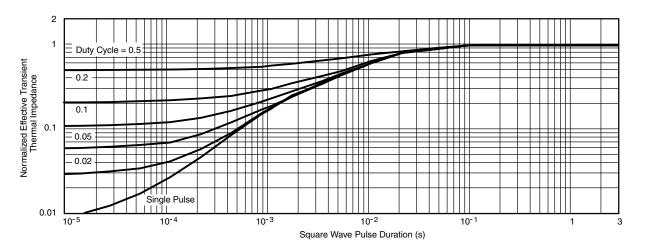
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

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THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

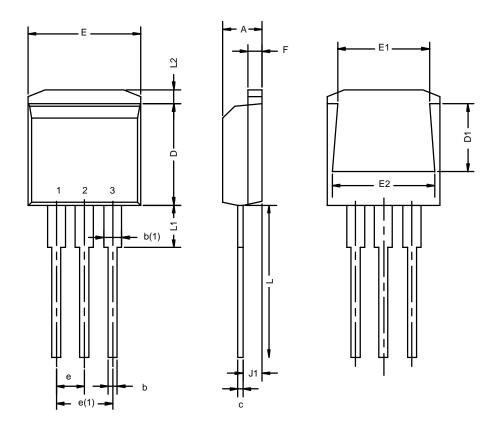
- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction to Ambient (25 °C)
- Normalized Transient Thermal Impedance Junction to Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?63402



TO-262: 3-LEAD



	MILLIM	ETERS*	INC	HES	
Dim	Min	Max	Min	Max	
Α	4.32	4.70	0.170	0.185	
b	0.64	1.00	0.025	0.039	
b(1)	1.14	1.40	0.045	0.055	
С	0.36	0.50	0.014	0.020	
D	8.64	9.65	0.340	0.380	
D1	5.59	6.10	0.220	0.240	
е	2.41	2.67	0.095	0.105	
e(1)	4.95	5.33	0.195	0.210	
Е	10.03	10.41	0.395	0.410	
E1	7.87	8.64	0.310	0.340	
E2	9.02	9.53	0.355	0.375	
F	1.14	1.40	0.045	0.055	
J1	2.41	2.79	0.095	0.110	
L	13.08	14.22	0.515	0.560	
L1	-	3.81	-	0.150	
L2	1.02	1.40	0.040	0.055	
ECN: T-02234—Rev. C, 14-Oct-02 DWG: 5855					

*Use millimeters as the primary measurement

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